

## AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

Claims 1-30 (Cancelled)

31. (New) A method comprising:

adding a first gas to an enclosure filled with a second gas through a vent, the first gas having a different composition than the second gas, and the enclosure being between a mask protective device, a patterned mask, and a wall connecting the mask protective device with the patterned mask; and

removing the second gas from the enclosure through the vent.

32. (New) The method of claim 31, wherein adding the first gas comprises adding the first gas through an inlet opening of the vent, and wherein removing the second gas comprises removing the second gas through an outlet opening of the vent.

33. (New) The method of claim 32, wherein adding comprises driving the first gas into the enclosure through the inlet opening by pressure, and wherein removing comprises simultaneously driving the second gas from the enclosure through the outlet opening by pressure.

34. (New) The method of claim 31, wherein adding the first gas comprises adding a molar quantity of gas substantially similar to a molar quantity of the second gas in the enclosure before the adding begins.

35. (New) The method of claim 31, wherein adding comprises adding a first gas that has a higher transmissivity for the photolithography radiation than the second gas.

36. (New) The method of claim 31, wherein:

adding the first gas comprises providing a higher concentration of the first gas on an outside of the enclosure than on an inside of the enclosure proximate the vent and adding the first gas to the enclosure by diffusion; and

removing the second gas comprises providing a lower concentration of the second gas on an outside of the enclosure than on an inside of the enclosure proximate the vent and removing the second gas from the enclosure by diffusion.

37. (New) The method of claim 36, wherein adding the first gas comprises adding the first gas through at least two openings of the vent, and wherein removing includes removing the second quantity of the second gas through at least two openings.

38. (New) The method of claim 31, further comprising transmitting radiation having a different wavelength than a wavelength of a photolithography radiation through the enclosure to increase a diffusion coefficient of a molecule in the enclosure.

39. (New) The method of claim 31, further comprising reducing a total pressure inside the enclosure to below 500 millimeters of mercury.

40. (New) The method of claim 31, wherein the first gas has a higher transmissivity for a photolithography radiation than the second gas.

41. (New) A method comprising:

attaching a mask protective device to a wall that is attached to a patterned mask, the attaching enclosing a volume of a second gas between the mask protective device and the patterned mask;

adding a first gas to the enclosed volume of the second gas, the first gas having a different composition than the second gas; and

removing the second gas from the enclosed volume.

42. (New) The method of claim 41, further comprising transmitting a photolithography radiation through the mask protective device.
43. (New) The method of claim 41, wherein attaching comprises attaching with an adhesive.